

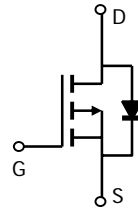
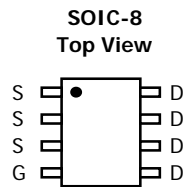
**AO4449**  
**P-Channel Enhancement Mode Field Effect Transistor**

**General Description**

The AO4449 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , and ultra-low low gate charge. This device is suitable for use as a load switch or in PWM applications. *Standard Product AO4449 is Pb-free (meets ROHS & Sony 259 specifications).*

**Features**

$V_{DS} (V) = -30V$   
 $I_D = -7 A (V_{GS} = -10V)$   
 $R_{DS(ON)} < 34m\Omega (V_{GS} = -10V)$   
 $R_{DS(ON)} < 54m\Omega (V_{GS} = -4.5V)$


**Absolute Maximum Ratings  $T_A=25^\circ C$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>F</sup>	$T_A=25^\circ C$ $T_A=70^\circ C$	$I_D$	-7
			-4.6
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	-40	A
Power Dissipation <sup>A</sup>	$T_A=25^\circ C$ $T_A=70^\circ C$	$P_D$	3.1
			2
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ C$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	31	40	$^\circ C/W$
$t \leq 10s$				
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JL}$	16	24	$^\circ C/W$
Steady-State				
Maximum Junction-to-Lead <sup>C</sup>				

Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
<b>STATIC PARAMETERS</b>							
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V	-30			V	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			-1 -5	μA	
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1	-2	-3	V	
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-5V	-40			A	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-7A T <sub>J</sub> =125°C		27 38	34	mΩ	
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-5A		43	54		
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-7A		15		S	
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V		-0.77	-1	V	
I <sub>S</sub>	Maximum Body-Diode Continuous Current				-3.5	A	
<b>DYNAMIC PARAMETERS</b>							
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =-15V, f=1MHz		980	1225	pF	
C <sub>oss</sub>	Output Capacitance				150		pF
C <sub>rss</sub>	Reverse Transfer Capacitance				115		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		2.2	3.3	Ω	
<b>SWITCHING PARAMETERS</b>							
Q <sub>g(10V)</sub>	Total Gate Charge (10V)	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-7A		18.7	24	nC	
Q <sub>g(4.5V)</sub>	Total Gate Charge (4.5V)				9.6		nC
Q <sub>gs</sub>	Gate Source Charge				3.2		nC
Q <sub>gd</sub>	Gate Drain Charge				4.8		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, R <sub>L</sub> =2.2Ω, R <sub>GEN</sub> =3Ω		7.7		ns	
t <sub>r</sub>	Turn-On Rise Time				6		ns
t <sub>D(off)</sub>	Turn-Off DelayTime				20		ns
t <sub>f</sub>	Turn-Off Fall Time				7		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =-7A, dI/dt=100A/μs		21	26	ns	
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =-7A, dI/dt=100A/μs		13		nC	

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The SOA curve provides a single pulse rating.

F: The current rating is based on the t ≤ 10s thermal resistance rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

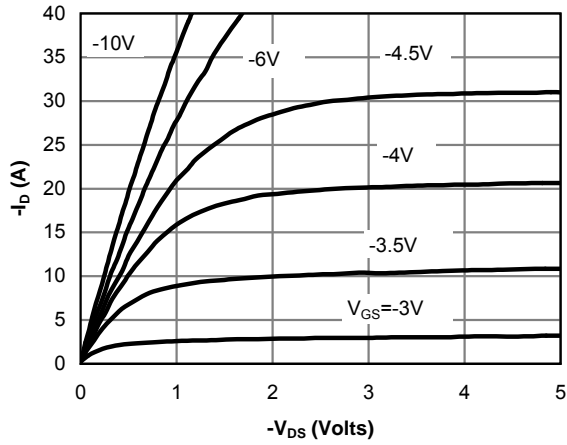


Figure 1: On-Region Characteristics

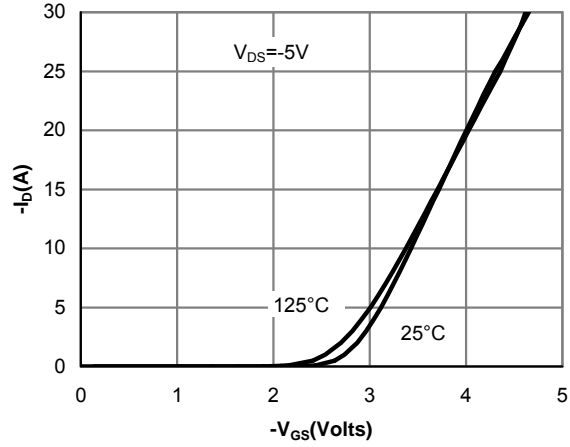


Figure 2: Transfer Characteristics

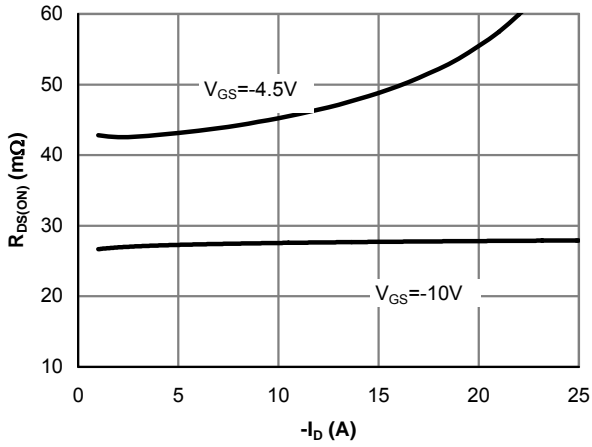


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

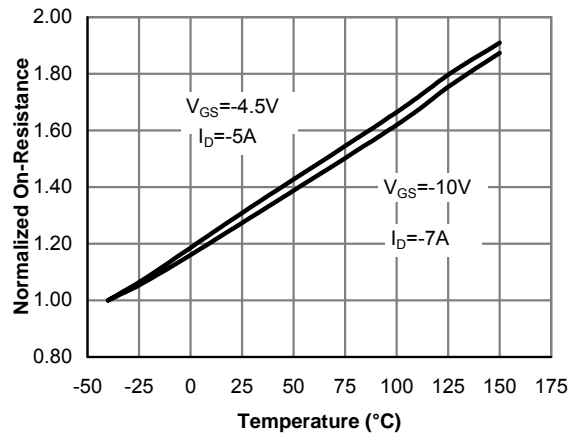


Figure 4: On-Resistance vs. Junction Temperature

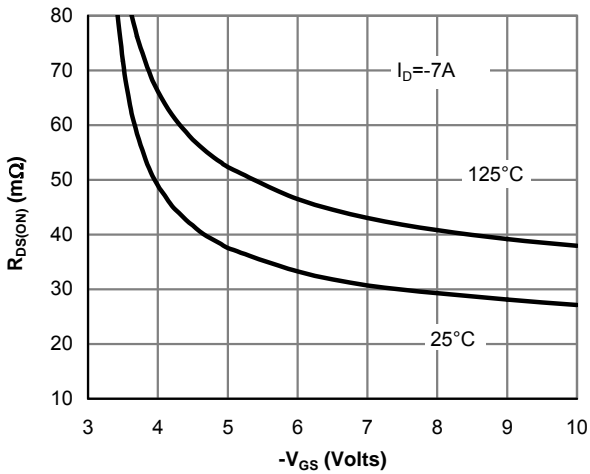


Figure 5: On-Resistance vs. Gate-Source Voltage

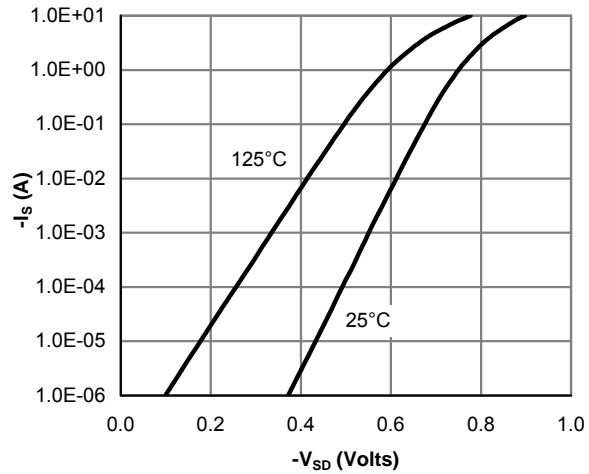


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

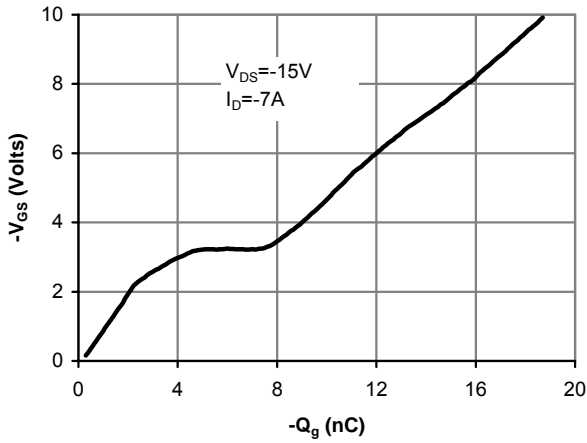


Figure 7: Gate-Charge Characteristics

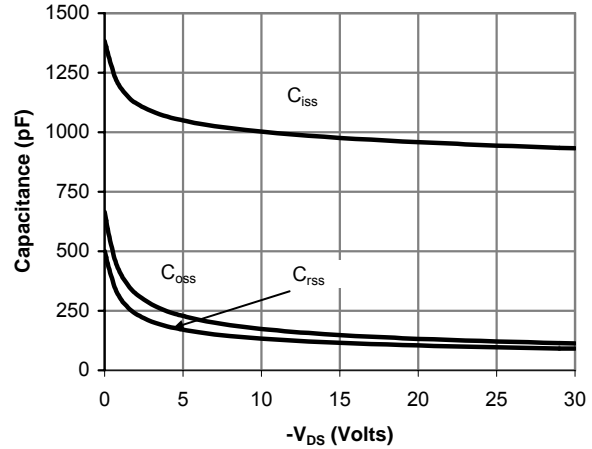


Figure 8: Capacitance Characteristics

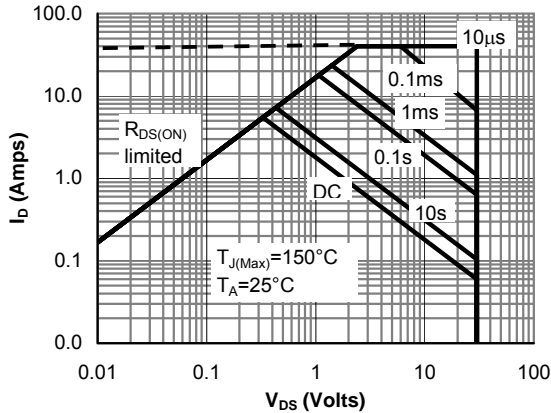


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

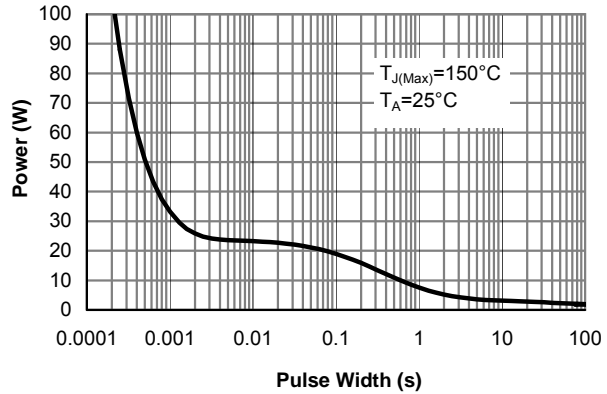


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

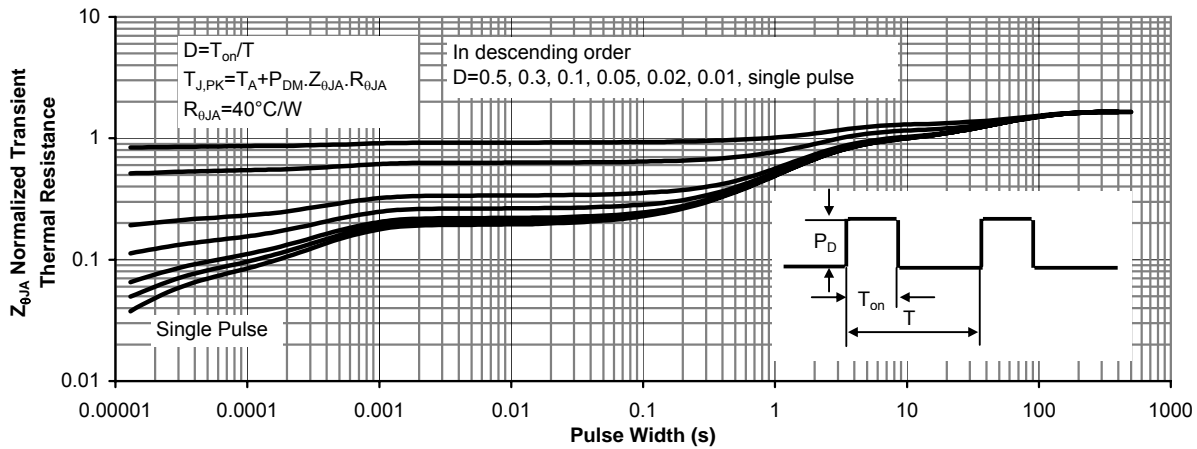


Figure 11: Normalized Maximum Transient Thermal Impedance